

NDS8410A

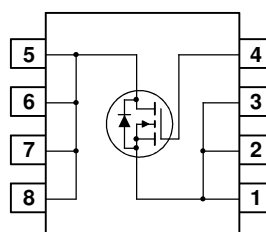
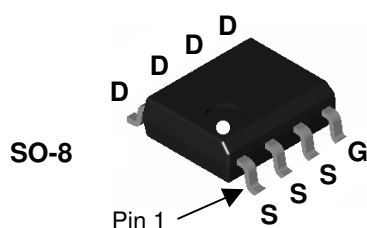
Single 30V N-Channel PowerTrench® MOSFET

General Description

This N-Channel MOSFET are produced using Fairchild's proprietary, high cell density, DMOS technology. This very high density process is especially tailored to minimize on-state resistance and provide superior switching performance. These devices are particularly suited for low voltage applications such as notebook computer power management and other battery powered circuits where fast switching, low in-line power loss, and resistance to transients are needed.

Features

- 10.8 A, 30 V $R_{DS(ON)} = 12\text{ m}\Omega @ V_{GS} = 10\text{ V}$
 $R_{DS(ON)} = 17\text{ m}\Omega @ V_{GS} = 4.5\text{ V}$
- Ultra-low gate charge
- High performance trench technology for extremely low $R_{DS(ON)}$
- High power and current handling capability



Absolute Maximum Ratings T_A=25°C unless otherwise noted

| Symbol | Parameter | Ratings | Units |
|-----------------------------------|--|---------------|-------|
| V _{DSS} | Drain-Source Voltage | 30 | V |
| V _{GSS} | Gate-Source Voltage | ±20 | |
| I _D | Drain Current – Continuous (Note 1a) | 10.8 | A |
| | | 50 | |
| P _D | Power Dissipation for Single Operation (Note 1a) | 2.5 | W |
| | | 1.2 (Note 1b) | |
| | | 1.0 (Note 1c) | |
| T _J , T _{STG} | Operating and Storage Junction Temperature Range | -55 to +150 | °C |

Thermal Characteristics

| | | | |
|------------------|---|----|------|
| R _{θJA} | Thermal Resistance, Junction-to-Ambient (Note 1a) | 50 | °C/W |
| R _{θJC} | Thermal Resistance, Junction-to-Ambient (Note 1) | 25 | |

Package Marking and Ordering Information

| Device Marking | Device | Reel Size | Tape width | Quantity |
|----------------|----------|-----------|------------|------------|
| NDS8410A | NDS8410A | 13" | 12mm | 2500 units |

Electrical Characteristics

$T_A = 25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Test Conditions | Min | Typ | Max | Units |
|--------|-----------|-----------------|-----|-----|-----|-------|
|--------|-----------|-----------------|-----|-----|-----|-------|

Off Characteristics

| | | | | | | |
|--------------------------------------|---|---|----|----|-----------|----------------------|
| BV_{DSS} | Drain–Source Breakdown Voltage | $V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$ | 30 | | | V |
| $\frac{\Delta BV_{DSS}}{\Delta T_J}$ | Breakdown Voltage Temperature Coefficient | $I_D = 250\ \mu\text{A}$, Referenced to 25°C | | 25 | | mV/ $^\circ\text{C}$ |
| I_{DSS} | Zero Gate Voltage Drain Current | $V_{DS} = 24\text{ V}, V_{GS} = 0\text{ V}$ | | | 1 | μA |
| | | $V_{DS} = 24\text{ V}, V_{GS} = 0\text{ V}, T_J = 55^\circ\text{C}$ | | | 10 | μA |
| I_{GSS} | Gate–Body Leakage | $V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}$ | | | ± 100 | nA |

On Characteristics (Note 2)

| | | | | | | |
|--|--|--|----|------|----|----------------------|
| $V_{GS(th)}$ | Gate Threshold Voltage | $V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$ | 1 | 2 | 3 | V |
| $\frac{\Delta V_{GS(th)}}{\Delta T_J}$ | Gate Threshold Voltage Temperature Coefficient | $I_D = 250\ \mu\text{A}$, Referenced to 25°C | | -4.9 | | mV/ $^\circ\text{C}$ |
| $R_{DS(on)}$ | Static Drain–Source On–Resistance | $V_{GS} = 10\text{ V}, I_D = 10.8\text{ A}$ | | 7.7 | 12 | m Ω |
| | | $V_{GS} = 4.5\text{ V}, I_D = 9\text{ A}$ | | 9.6 | 17 | |
| | | $V_{GS} = 10\text{ V}, I_D = 10.8\text{ A}, T_J = 125^\circ\text{C}$ | | 10.7 | 22 | |
| $I_{D(on)}$ | On–State Drain Current | $V_{GS} = 10\text{ V}, V_{DS} = 5\text{ V}$ | 50 | | | A |
| g_{FS} | Forward Transconductance | $V_{DS} = 10\text{ V}, I_D = 10.8\text{ A}$ | | 55 | | S |

Dynamic Characteristics

| | | | | | | |
|-----------|------------------------------|---|--|------|--|----------|
| C_{iss} | Input Capacitance | $V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V}, f = 1.0\text{ MHz}$ | | 1620 | | pF |
| C_{oss} | Output Capacitance | | | 380 | | pF |
| C_{rss} | Reverse Transfer Capacitance | | | 160 | | pF |
| R_G | Gate Resistance | $V_{GS} = 15\text{ mV}, f = 1.0\text{ MHz}$ | | 1.3 | | Ω |

Switching Characteristics (Note 2)

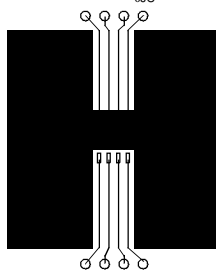
| | | | | | | |
|--------------|---------------------|---|--|-----|----|----|
| $t_{d(on)}$ | Turn–On Delay Time | $V_{DD} = 15\text{ V}, I_D = 1\text{ A}, V_{GS} = 10\text{ V}, R_{GEN} = 6\ \Omega$ | | 10 | 19 | ns |
| t_r | Turn–On Rise Time | | | 6 | 22 | ns |
| $t_{d(off)}$ | Turn–Off Delay Time | | | 27 | 45 | ns |
| t_f | Turn–Off Fall Time | | | 12 | 27 | ns |
| Q_g | Total Gate Charge | $V_{DS} = 15\text{ V}, I_D = 10.8\text{ A}, V_{GS} = 5\text{ V}$ | | 16 | 22 | nC |
| Q_{gs} | Gate–Source Charge | | | 4.8 | | nC |
| Q_{gd} | Gate–Drain Charge | | | 5.6 | | nC |

Drain–Source Diode Characteristics and Maximum Ratings

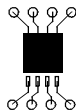
| | | | | | | |
|----------|---|---|--|------|-----|----|
| I_S | Maximum Continuous Drain–Source Diode Forward Current | | | 2.1 | A | |
| V_{SD} | Drain–Source Diode Forward Voltage | $V_{GS} = 0\text{ V}, I_S = 2.1\text{ A}$ (Note 2) | | 0.82 | 1.2 | V |
| t_{rr} | Diode Reverse Recovery Time | $I_F = 10.8\text{ A}, d_I/d_t = 100\text{ A}/\mu\text{s}$ | | 28 | | nS |
| Q_{rr} | Diode Reverse Recovery Charge | | | 18 | | nC |

Notes:

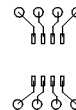
1. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a) $50^\circ\text{C}/\text{W}$ when mounted on a 1 in^2 pad of 2 oz copper



b) $105^\circ\text{C}/\text{W}$ when mounted on a $.04\text{ in}^2$ pad of 2 oz copper



c) $125^\circ\text{C}/\text{W}$ when mounted on a minimum pad.

Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width < $300\ \mu\text{s}$, Duty Cycle < 2.0%

Typical Characteristics

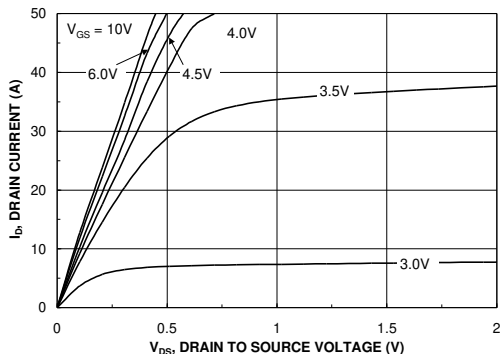


Figure 1. On-Region Characteristics.

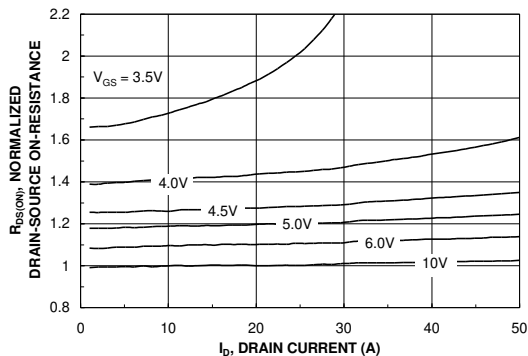


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

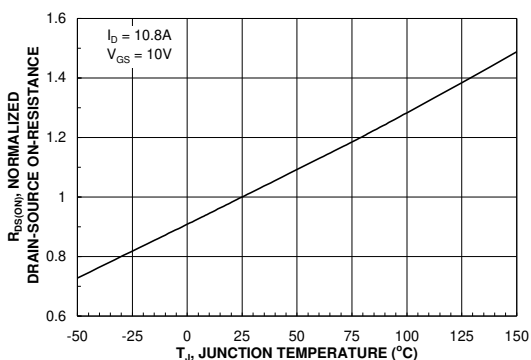


Figure 3. On-Resistance Variation with Temperature.

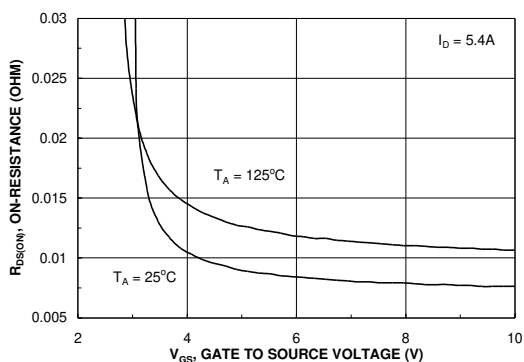


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

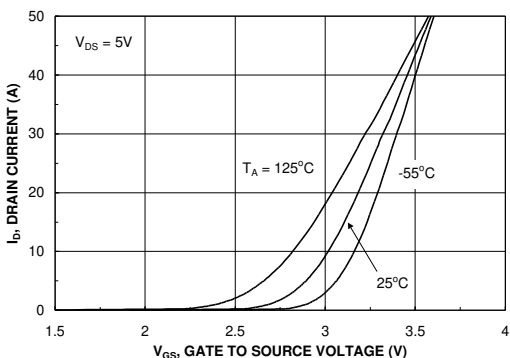


Figure 5. Transfer Characteristics.

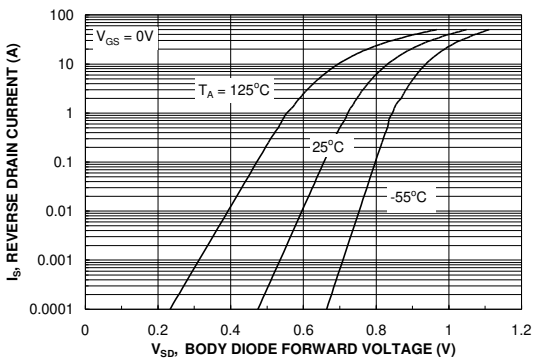


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics

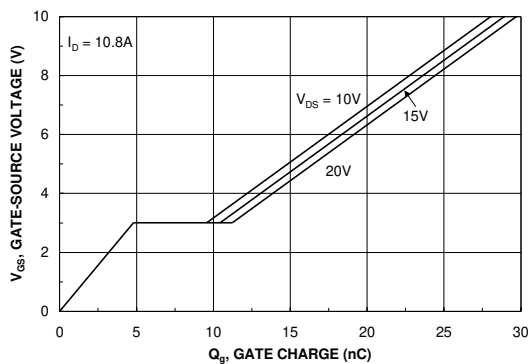


Figure 7. Gate Charge Characteristics.

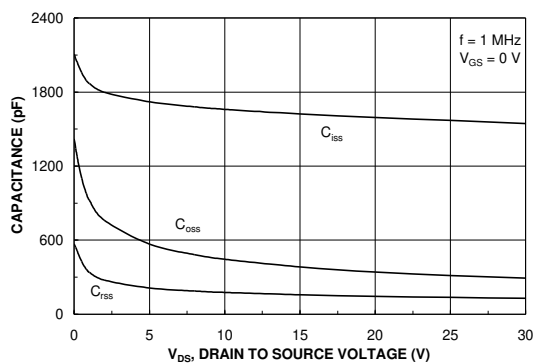


Figure 8. Capacitance Characteristics.

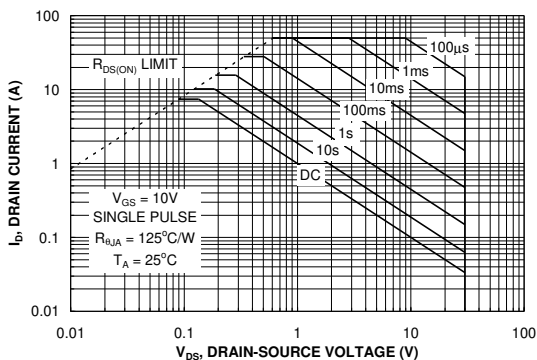


Figure 9. Maximum Safe Operating Area.

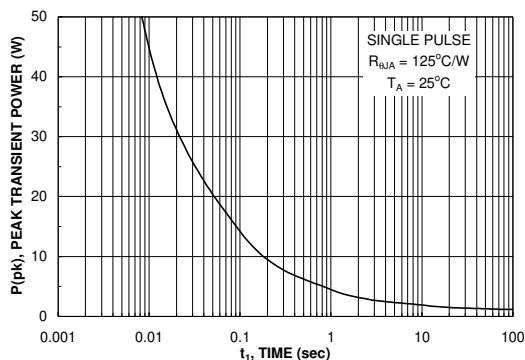


Figure 10. Single Pulse Maximum Power Dissipation.

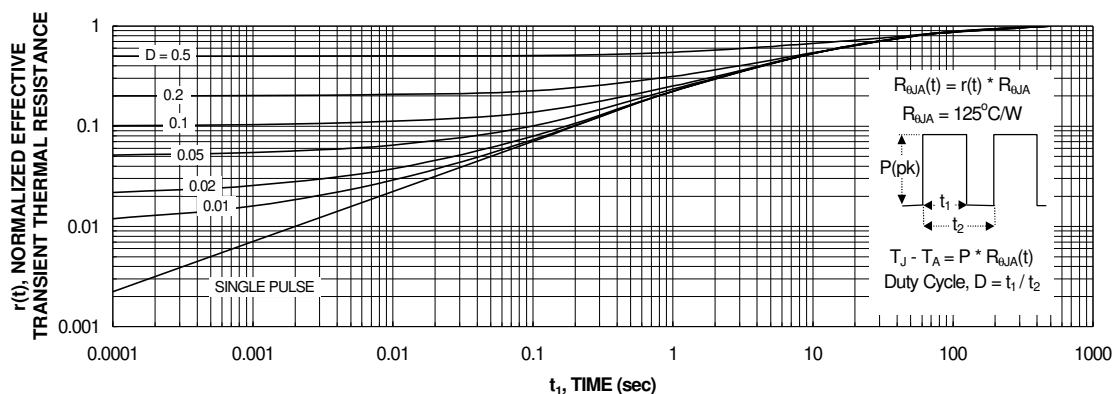


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c. Transient thermal response will change depending on the circuit board design.

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